



# 제 29회 한국반도체학술대회

The 29th Korean Conference on Semiconductors

2022년 1월 24일(월)~ 26일(수) | 강원도 하이원 그랜드호텔(컨벤션타워)

2022년 1월 26일(수), 09:00-10:30

Room B (에메랄드 II+III, 5층)

## D. Thin Film Process Technology 분과

### [WB1-D] Two-dimensional Materials

좌장: 김성근 책임(KIST), 안지훈 교수(한양대학교)

<p><b>WB1-D-1</b> 09:00-09:30</p>	<p><b>Heterojunction Band Engineering for vdW Electronics &amp; Optoelectronics</b> Chul-Ho Lee<sup>1,2</sup> <sup>1</sup><i>KU-KIST Graduate School of Converging Science and Technology, Korea University</i> <sup>2</sup><i>Department of Integrative Energy Engineering, Korea University</i></p>
<p><b>WB1-D-2</b> 09:30-09:45</p>	<p><b>Wafer-scale Crystalline MoS<sub>2</sub> Thin Films with Controlled Morphology Using Pulsed Metal-organic Chemical Vapor Deposition at Low Temperature</b> Jeong-Hun Choi, Min-Ji Ha, and Ji-Hoon Ahn <i>Department of Materials Science and Chemical Engineering, Hanyang University</i></p>
<p><b>WB1-D-3</b> 09:45-10:00</p>	<p><b>Two-dimensional Electron Gas for Conductive Bridge Random Access Memory</b> Ju Young Sung<sup>1,2</sup>, Chang Hee Ko<sup>1,2</sup>, Chae Hyun Lee<sup>1,2</sup>, Tae Jun Seok<sup>3,4</sup>, Ji Hyeon Choi<sup>3,4</sup>, Tae Joo Park<sup>3,4</sup>, and Sang Woon Lee<sup>1,2</sup> <sup>1</sup><i>Department of Energy Systems Research, Ajou University</i>, <sup>2</sup><i>Department of Physics, Ajou University</i>, <sup>3</sup><i>Department of Materials Science &amp; Chemical Engineering, Hanyang University</i>, <sup>4</sup><i>Department of Advanced Materials Engineering, Hanyang University</i></p>
<p><b>WB1-D-4</b> 10:00-10:15</p>	<p><b>Two-Step Atomic-Layer-Deposited GeSe<sub>2</sub> for High-Performance Ovonic Threshold Switch</b> Woohyun Kim<sup>1</sup>, Chanyoung Yoo<sup>1</sup>, Jeong Woo Jeon<sup>1</sup>, Wonho Choi<sup>1</sup>, Byongwoo Park<sup>1</sup>, Gwang Sik Jeon<sup>1</sup>, Sangmin Jeon<sup>1</sup>, Yoon Kyeung Lee<sup>2</sup>, and Cheol Seong Hwang<sup>1</sup> <sup>1</sup><i>Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University</i>, <sup>2</sup><i>Division of Advanced Materials Engineering, Jeonbuk National University</i></p>
<p><b>WB1-D-5</b> 10:15-10:30</p>	<p><b>Temperature-Dependent Growth of Tin Selenide (Sn<sub>x</sub>Se<sub>1-x</sub>) Thin Films by Atomic Layer Deposition</b> Jeong Woo Jeon<sup>1</sup>, Chanyoung Yoo<sup>1</sup>, Woohyun Kim<sup>1</sup>, Wonho Choi<sup>1</sup>, Byongwoo Park<sup>1</sup>, Gwangsik Jeon<sup>1</sup>, Sangmin Jeon<sup>1</sup>, Yoon Kyeung Lee<sup>2</sup>, and Cheol Seong Hwang<sup>1</sup> <sup>1</sup><i>Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University</i>, <sup>2</sup><i>Division of Advanced Materials Engineering, Jeonbuk National University</i></p>